74HC1G32-Q100; 74HCT1G32-Q100

2-input OR gate

Rev. 1 — 8 August 2012

Product data sheet

1. General description

74HC1G32-Q100 and 74HCT1G32-Q100 are high-speed Si-gate CMOS devices. They provide a 2-input OR function.

The standard output currents are half of those of the 74HC32-Q100 and 74HCT32-Q100.

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 1) and is suitable for use in automotive applications.

2. Features and benefits

- Automotive product qualification in accordance with AEC-Q100 (Grade 1)
 - ◆ Specified from -40 °C to +85 °C and from -40 °C to +125 °C
- Input levels:
 - ◆ For 74HC1G32-Q100: CMOS level
 - ◆ For 74HCT1G32-Q100: TTL level
- Symmetrical output impedance
- High noise immunity
- Low power dissipation
- Balanced propagation delays
- ESD protection:
 - ◆ MIL-STD-883, method 3015 exceeds 2000 V
 - ◆ HBM JESD22-A114F exceeds 2000 V
 - ♦ MM JESD22-A115-A exceeds 200 V (C = 200 pF, R = 0 Ω)
- SOT353-1 and SOT753 package options

3. Ordering information

Table 1. Ordering information

Type number	Package	Package				
	Temperature range	Name	Description	Version		
74HC1G32GW-Q100	–40 °C to +125 °C	TSSOP5	,			
74HCT1G32GW-Q100			body width 1.25 mm			
74HC1G32GV-Q100	–40 °C to +125 °C	SC-74A	plastic surface-mounted package; 5 leads	SOT753		
74HCT1G32GV-Q100						



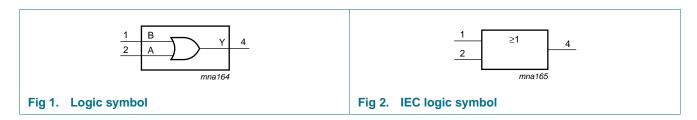
4. Marking

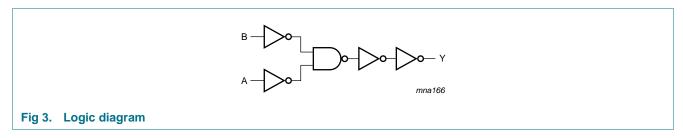
Table 2. Marking codes

Type number	Marking code ^[1]
74HC1G32GW-Q100	HG
74HCT1G32GW-Q100	TG
74HC1G32GV-Q100	H32
74HCT1G32GV-Q100	T32

^[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

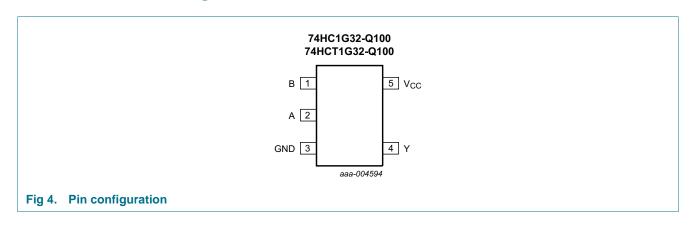
5. Functional diagram





6. Pinning information

6.1 Pinning



6.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
В	1	data input B
A	2	data input A
GND	3	ground (0 V)
Υ	4	data output Y
V _{CC}	5	supply voltage

7. Functional description

Table 4. Function table

H = HIGH voltage level; L = LOW voltage level

Inputs		Output
Α	В	Υ
L	L	L
L	Н	Н
Н	L	Н
Н	Н	Н

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V). [1]

					-
Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	+7.0	V
I _{IK}	input clamping current	$V_I < -0.5 \text{ V or } V_I > V_{CC} + 0.5 \text{ V}$	-	±20	mA
I _{OK}	output clamping current	V_O < -0.5 V or V_O > V_{CC} + 0.5 V	-	±20	mA
Io	output current	$-0.5 \text{ V} < \text{V}_{\text{O}} < \text{V}_{\text{CC}} + 0.5 \text{ V}$	-	±12.5	mA
I _{CC}	supply current		-	25	mA
I_{GND}	ground current		-25	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	$T_{amb} = -40 ^{\circ}\text{C} \text{ to } +125 ^{\circ}\text{C}$	[2] _	200	mW

^[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

^[2] Above 55 $^{\circ}$ C the value of P_{tot} derates linearly with 2.5 mW/K.

9. Recommended operating conditions

Table 6. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V).

Symbol	I Parameter Conditions		74H	C1G32-0	2100	74H0	CT1G32-0	Q100	Unit
			Min	Тур	Max	Min	Тур	Max	
V_{CC}	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
VI	input voltage		0	-	V_{CC}	0	-	V_{CC}	V
Vo	output voltage		0	-	V_{CC}	0	-	V_{CC}	V
T _{amb}	ambient temperature		-40	+25	+125	-40	+25	+125	°C
$\Delta t / \Delta V$	input transition rise	$V_{CC} = 2.0 \text{ V}$	-	-	625	-	-	-	ns/V
and fall rate	and fall rate	V _{CC} = 4.5 V	-	-	139	-	-	139	ns/V
		V _{CC} = 6.0 V	-	-	83	-	-	-	ns/V

10. Static characteristics

Table 7. Static characteristics

Voltages are referenced to GND (ground = 0 V). All typical values are measured at T_{amb} = 25 °C.

Symbol	Parameter	Conditions	-40	°C to +8	35 °C	–40 °C t	o +125 °C	Unit
			Min	Тур	Max	Min	Max	
74HC1G3	2-Q100			•				
V_{IH}	HIGH-level input	V _{CC} = 2.0 V	1.5	1.2	-	1.5	-	V
	voltage	V _{CC} = 4.5 V	3.15	2.4	-	3.15	-	V
		V _{CC} = 6.0 V	4.2	3.2	-	4.2	-	V
V_{IL}	/ _{IL} LOW-level input voltage	V _{CC} = 2.0 V	-	0.8	0.5	-	0.5	V
		V _{CC} = 4.5 V	-	2.1	1.35	-	1.35	V
	V _{CC} = 6.0 V	-	2.8	1.8	-	1.8	V	
V_{OH}	HIGH-level output	$V_I = V_{IH}$ or V_{IL}						
voltage	voltage	$I_{O} = -20 \mu A; V_{CC} = 2.0 V$	1.9	2.0	-	1.9	-	V
		$I_O = -20 \mu A; V_{CC} = 4.5 V$	4.4	4.5	-	4.4	-	V
		$I_O = -20 \mu A; V_{CC} = 6.0 V$	5.9	6.0	-	5.9	-	V
		$I_O = -2.0$ mA; $V_{CC} = 4.5$ V	4.13	4.32	-	3.7	-	V
		$I_{O} = -2.6 \text{ mA}; V_{CC} = 6.0 \text{ V}$	5.63	5.81	-	5.2	-	V
V_{OL}	LOW-level output	$V_I = V_{IH}$ or V_{IL}						
	voltage	$I_O = 20 \mu A; V_{CC} = 2.0 V$	-	0	0.1	-	0.1	V
		$I_O = 20 \mu A; V_{CC} = 4.5 V$	-	0	0.1	-	0.1	V
		$I_O = 20 \mu A; V_{CC} = 6.0 V$	-	0	0.1	-	0.1	V
		$I_O = 2.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	0.15	0.33	-	0.4	V
		$I_O = 2.6 \text{ mA}; V_{CC} = 6.0 \text{ V}$	-	0.16	0.33	-	0.4	V
I _I	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 6.0 \text{ V}$	-	-	1.0	-	1.0	μΑ
I _{CC}	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 6.0 \text{ V}$	-	-	10	-	20	μА
Cı	input capacitance		-	1.5	-	-	-	pF

 Table 7.
 Static characteristics ...continued

Voltages are referenced to GND (ground = 0 V). All typical values are measured at T_{amb} = 25 °C.

Symbol	Parameter	Conditions		–40 °C to +85 °C			-40 °C to +125 °C		
-			Min	Тур	Max	Min	Max		
74HCT1G	32-Q100					I			
V_{IH}	HIGH-level input voltage	$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	2.0	1.6	-	2.0	-	V	
V_{IL}	LOW-level input voltage	$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	-	1.2	8.0	-	0.8	V	
V _{OH}	HIGH-level output	$V_I = V_{IH}$ or V_{IL} ; $V_{CC} = 4.5 \text{ V}$							
	voltage	$I_{O} = -20 \mu A$	4.4	4.5	-	4.4	-	V	
		$I_{O} = -2.0 \text{ mA}$	4.13	4.32	-	3.7	-	V	
V _{OL}	LOW-level output	$V_I = V_{IH}$ or V_{IL} ; $V_{CC} = 4.5 \text{ V}$							
	voltage	I _O = 20 μA	-	0	0.1	-	0.1	V	
		$I_{O} = 2.0 \text{ mA}$	-	0.15	0.33	-	0.4	V	
II	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 5.5 \text{ V}$	-	-	1.0	-	1.0	μΑ	
I _{CC}	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 5.5 \text{ V}$	-	-	10	-	20	μΑ	
ΔI_{CC}	additional supply current	per input; $V_{CC} = 4.5 \text{ V to } 5.5 \text{ V};$ $V_I = V_{CC} - 2.1 \text{ V}; I_O = 0 \text{ A}$	-	-	500	-	850	μΑ	
Cı	input capacitance		-	1.5	-	-	-	pF	

11. Dynamic characteristics

Table 8. Dynamic characteristics

GND = 0 V; $t_r = t_f \le 6.0$ ns. All typical values are measured at $T_{amb} = 25$ °C. For test circuit see <u>Figure 6</u>

Symbol	mbol Parameter Conditions		-40 °C to +85 °C			–40 °C t	Unit		
				Min	Тур	Max	Min	Max	
74HC1G	32-Q100						'	1	
t _{pd}	propagation delay	A and B to Y; see Figure 5	<u>[1]</u>						
		$V_{CC} = 2.0 \text{ V}; C_L = 50 \text{ pF}$		-	18	115	-	135	ns
		$V_{CC} = 4.5 \text{ V}; C_L = 50 \text{ pF}$		-	8	23	-	27	ns
		$V_{CC} = 5.0 \text{ V}; C_L = 15 \text{ pF}$		-	8	-	-	-	ns
		$V_{CC} = 6.0 \text{ V}; C_L = 50 \text{ pF}$		-	7	20	-	23	ns
C_{PD}	power dissipation capacitance	$V_I = GND \text{ to } V_{CC}$	[2]	-	19	-	-	-	pF

 Table 8.
 Dynamic characteristics ...continued

GND = 0 V; $t_r = t_f \le 6.0$ ns. All typical values are measured at $T_{amb} = 25$ °C. For test circuit see Figure 6

	, , ,	71	arrio						
Symbol Parameter Conditions			-40 °C to +85 °C			–40 °C t	Unit		
			Ī	Min	Тур	Max	Min	Max	
74HCT1	G32-Q100		,		'	•	'		
t _{pd}	propagation delay	A and B to Y; see Figure 5	<u>[1]</u>						
		$V_{CC} = 4.5 \text{ V}; C_L = 50 \text{ pF}$		-	10	24	-	27	ns
		$V_{CC} = 5.0 \text{ V}; C_L = 15 \text{ pF}$		-	10	-	-	-	ns
C_{PD}	power dissipation capacitance	$V_I = GND \text{ to } V_{CC} - 1.5 \text{ V}$	[2]	-	20	-	-	-	pF

- [1] t_{pd} is the same as t_{PLH} and t_{PHL} .
- [2] C_{PD} is used to determine the dynamic power dissipation P_D (μW).

 $P_D = C_{PD} \times V_{CC}{}^2 \times f_i + \sum \left(C_L \times V_{CC}{}^2 \times f_o \right)$ where:

 f_i = input frequency in MHz

fo = output frequency in MHz

 C_L = output load capacitance in pF

V_{CC} = supply voltage in V

 $\sum (C_L \times V_{CC}^2 \times f_o) = \text{sum of outputs}$

12. Waveforms

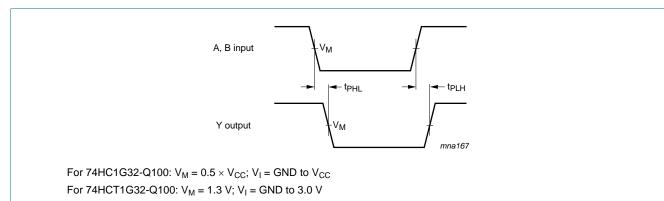
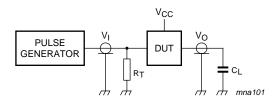


Fig 5. The input (A and B) to output (Y) propagation delays



Measurement points are given in Table 8. Definitions for test circuit:

C_L = Load capacitance including jig and probe capacitance.

 R_T = Termination resistance should be equal to output impedance Z_0 of the pulse generator.

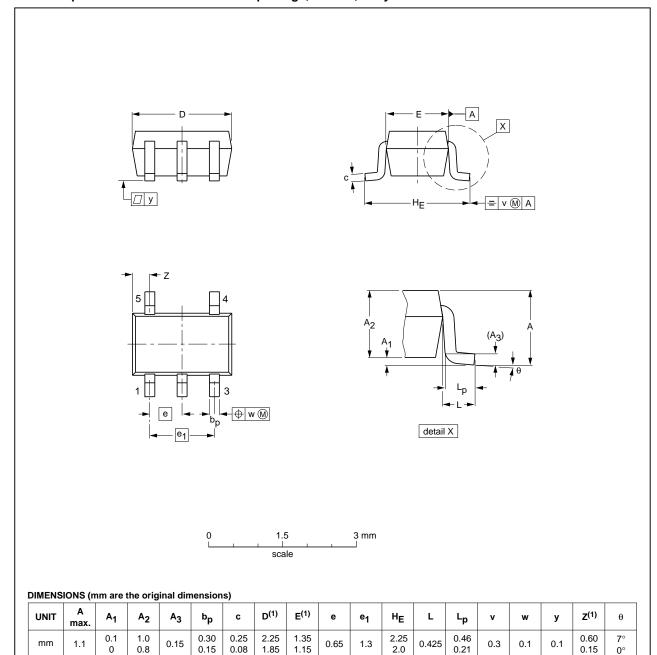
Fig 6. Load circuitry for switching times

74HC_HCT1G32_Q100

13. Package outline

TSSOP5: plastic thin shrink small outline package; 5 leads; body width 1.25 mm

SOT353-1



1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA	PROJECTION ISSUE DA	
SOT353-1		MO-203	SC-88A		-00-09-01- 03-02-19

Fig 7. Package outline SOT353-1 (TSSOP5)

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Plastic surface-mounted package; 5 leads

SOT753

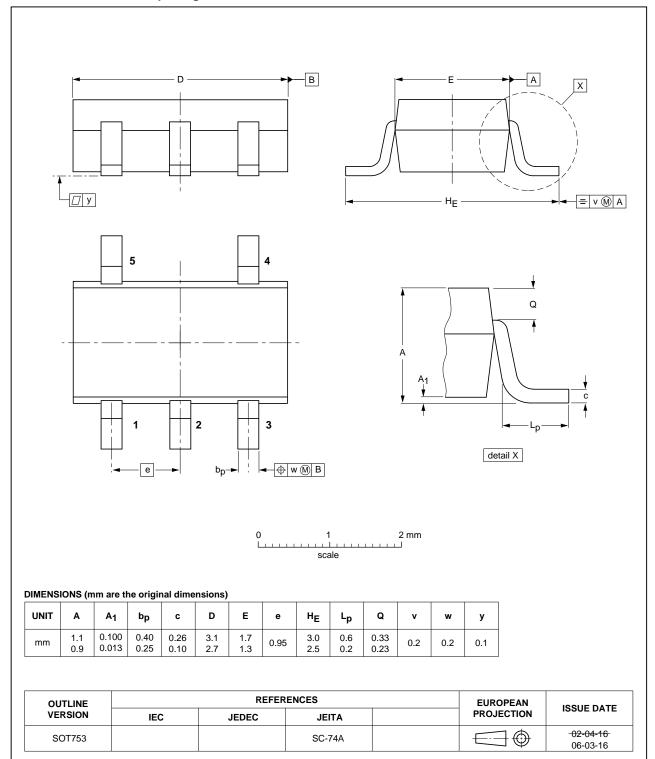


Fig 8. Package outline SOT753 (SC-74A)

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14. Abbreviations

Table 9. Abbreviations

Acronym	Description
CMOS	Complementary Metal Oxide Semiconductor
TTL	Transistor-Transistor Logic
НВМ	Human Body Model
ESD	ElectroStatic Discharge
MM	Machine Model
DUT	Device Under Test
MIL	Military

15. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74HC_HCT1G32_Q100 v.1	20120808	Product data sheet	-	-

16. Legal information

16.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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